

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**DECLARATION FOR PATENT APPLICATION**

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled:

METHOD OF MAKING A MEMORY CELL CAPACITOR WITH  
 $Ta_2O_5$  DIELECTRIC

the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by an amendment, if any, specifically referred to in this oath or declaration.

I acknowledge the duty to disclose all information known to me which is material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code § 119/365 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

Prior Foreign Application(s)			<u>Priority Not Claimed</u>
(Number)	(Country)	(Filing Date)	<input type="checkbox"/>
<input type="text"/>	<input type="text"/>	<input type="text"/>	<input type="checkbox"/>
<input type="text"/>	<input type="text"/>	<input type="text"/>	<input type="checkbox"/>
<input type="text"/>	<input type="text"/>	<input type="text"/>	<input type="checkbox"/>

I hereby claim the benefit under Title 35, United States Code, § 120/365 of any United States and PCT international application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior

United States application in the manner provided by the first paragraph of Title 35, United States Code, § 112, I acknowledge the duty to disclose all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56(a) which became available between the filing date of the prior application and the national or PCT international filing date of this application:

(Application No.)	(Filing Date)	(Status) (patented, pending, abandoned)
(Application No.)	(Filing Date)	(Status) (patented, pending, abandoned)
(Application No.)	(Filing Date)	(Status) (patented, pending, abandoned)

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Please address all correspondence to Thomas J. D'Amico of Dickstein Shapiro Morin & Oshinsky LLP located at 2101 L Street NW, Washington, DC 20037-1526. Telephone calls should be made to (202) 785-9700.

Full name of sole inventor: Weimin Li

Inventor's signature:



Date: 4/23/2002

Residence: Boise, Idaho

Citizenship: China

Mailing Address: 14124 W. Chadford Dr.  
Boise, Idaho 83713

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Weimin Li

Application No.: Not Yet Assigned

Group Art Unit: N/A

Filed: To Be Filed Concurrently Herewith

Examiner: Not Yet Assigned

For: METHOD OF MAKING A MEMORY  
CELL CAPACITOR WITH Ta<sub>2</sub>O<sub>5</sub>  
DIELECTRIC

**POWER OF ATTORNEY BY ASSIGNEE AND**  
**CERTIFICATE BY ASSIGNEE UNDER 37 CFR § 3.73(B)**

Assistant Commissioner for Patents  
Washington, DC 20231

Dear Sir:

Micron Technology, Inc., Assignee of the entire right, title and interest in the above-identified application by virtue of the Assignment attached hereto (which is also being submitted concurrently for recordation), hereby appoints the attorneys and agents of the firm of Dickstein Shapiro Morin & Oshinsky LLP located at 2101 L Street NW, Washington, DC 20037-1526, listed as follows:

Gary M. Hoffman	26,411	John C. Luce	34,378	Ellen S. Tao	43,383
Thomas J. D'Amico	28,371	Peter McGee	35,947	Gary L. Veron	39,057
Donald A. Gregory	28,954	Edward A. Meilman	24,735	Steven I. Weisburd	27,409
James W. Brady, Jr.	32,115	Edwin Oh	45,319	Mialecka C. Williams-Bibbs	48,037
Jon D. Grossman	32,699	William E. Powell, III	39,803	Jeremy A. Cubert	40,399
Mark J. Thronson	33,082	Steven Rubin	43,063	Gianni Minutoli	41,198
Eric Oliver	35,307	Michael J. Scheer	34,425	Michael Bergman	42,318
Laurence E. Fisher	37,131	Patrick T. Skacel	47,948	Salvatore P. Tamburo	45,153
Ryan H. Flax	48,141	Stephen A. Soffen	31,063	Peter Veytsman	45,920
Richard LaCava	41,135	Christopher M. Tanner	41,518	Christopher S. Chow	46,493

and also, listed as follows:

Application No.: Not signed

DC No.: M4065.0541/P541

Charles B. Brantley, III	38,086	Kevin D. Martin	37,882	David J. Paul	34,692
Michael L. Lynch	30,871				

attorneys of Micron Technology, Inc. as its attorneys with full power of substitution to prosecute this application and to transact all business in the Patent and Trademark Office in connection therewith.

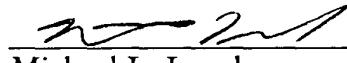
The Assignee certifies that the above-identified assignment has been reviewed and to the best of the Assignee's knowledge and belief, title is in the assignee.

Please direct all correspondence regarding this application to the following:

Thomas J. D'Amico  
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Fax: (202) 887-0689

Respectfully submitted,

MICRON TECHNOLOGY, INC.

  
\_\_\_\_\_  
Michael L. Lynch  
Chief Patent Counsel  
Registration No. 30,871

Dated: 4-29-02